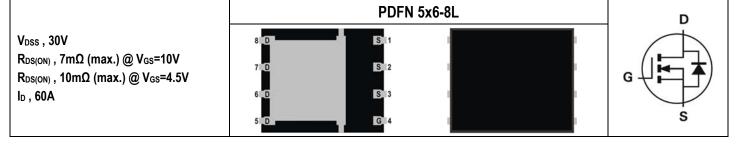


SG30N09Q

30V N-Channel Power MOSFET



Description	Features
The SG30N09Q uses advanced Trench technology and designs to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	 Low On-Resistance Low Input Capacitance Low Miller Charge Low Input / Output Leakage Pb-free lead plating; RoHS compliant
	Applications
	Motor / Body Load Control
	Automotive Systems
	Load Switch
	DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG30N09Q	Halogen-Free	PDFN 5x6-8L	Q	Tape & Reel	2,500

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	30	V
Gate-Source Voltage		Vgs	±20	V
Drain Current Continuous	Tc=25°C		60	А
Drain Current-Continuous	T _c =100°C	lD	47	A
Drain Current-Pulsed Note 1		Ідм	120	А
Avalanche Current		las	35	А
Avalanche Energy, L=0.1mH		E _{AS}	61.25	mJ
Maximum Bawar Dissinction	Tc=25°C		55.6	W
Maximum Power Dissipation	Tc=100°C		27.8	W
Operating Junction Temperature Range	·	TJ TSTG	-55 to +175	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	R _{0JA}	Steady State	-	-	62	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	2.7	°C/W



Electrical Characteristics (T_=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BVDSS	V _{GS} =0V, I _{DS} =250µA	30	-	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage	lgss	$V_{GS}=\pm 20V$, $V_{DS}=0V$	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250µA	1.2	-	2.5	V
Drain-Source On-State Resistance	D	V _{GS} =10V, I _{DS} =30A	-	-	7	mΩ
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =4.5V, I _{DS} =15A	-	-	10	mΩ
Forward Transconductance	g fs	V _{DS} =5V, I _D =30A	-	36	-	S

DYNAMIC CHARACTERISTICS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Input Capacitance	C _{iss}		-	1290	-		
Output Capacitance	Coss	V _{DS} =15V, V _{GS} =0V, f=1MHz	-	159	-	pF	
Reverse Transfer Capacitance	Crss		-	128	-		
Gate Resistance	Rg	V_{GS} =0V, V_{DS} =0V, f=1MHz	-	1.5	-	Ω	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	4.5	-	
Rise Time	tr	V _{DD} =15V, I _D =15A, V _{GS} =10V,	-	11.9	-	
Turn-Off Delay Time	T _{d(off)}	Rg=3.3Ω	-	26	-	ns
Fall Time	tr		-	7.8	-	
Total Gate Charge	Qg		-	12.3	-	
Gate to Source Gate Charge	Q _{gs}	V _{DS} =15V, I _{DS} =15A, V _{GS} =4.5V	-	4.1	-	nC
Gate to Drain "Miller" Charge	Qgd		-	5	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Body-Diode Continuous Current	ls	V _G =V _D =0V, Force Current	-	-	60	Α
Pulsed Source Current	I _{SM}	V _G =V _D =0V, Force Current	-	-	120	Α
Drain-Source Diode Forward Voltage	Vsd	V _{GS} =0V, I _S =1A	-	0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	V _{DD} =15V, I _F =30A, di/dt=100A/µs	-	9	-	ns
Body Diode Reverse Recovery Charge	Qrr	V_{DD} =15V, I _F =30A, di/dt=100A/µs	-	2	-	nC

Notes:

1. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

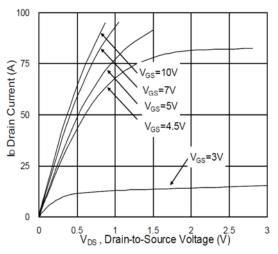
 R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0JC} is guaranteed by design while R_{0JA} is determined by the user's board design. R_{0JA} shown below for single device operation on FR-4 in still air.



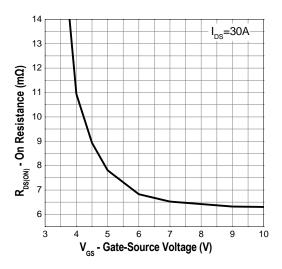
SG30N09Q 30V N-Channel Power MOSFET

Typical Operating Characteristics

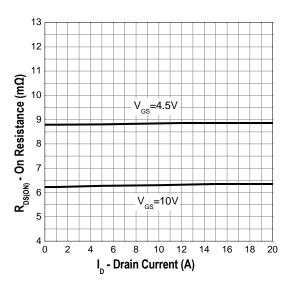
Output Characteristics



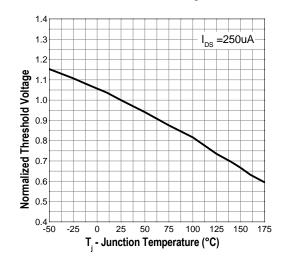
Gate-Source On Resistance



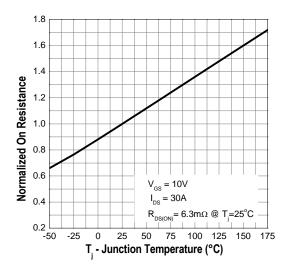
Drain-Source On Resistance



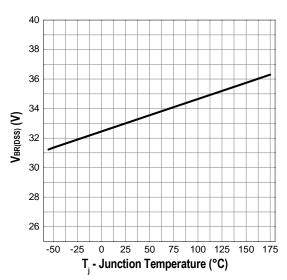
Gate Threshold Voltage



Drain-Source On Resistance

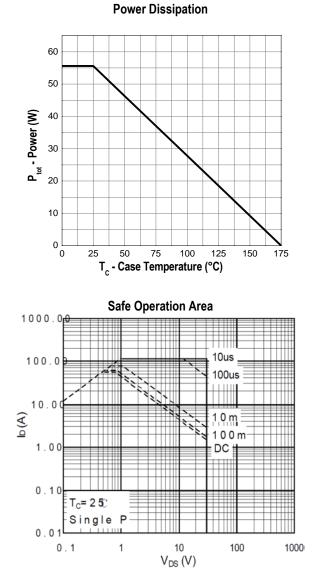




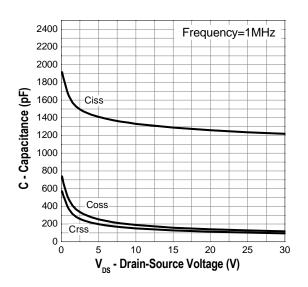




Typical Operating Characteristics (Cont.)



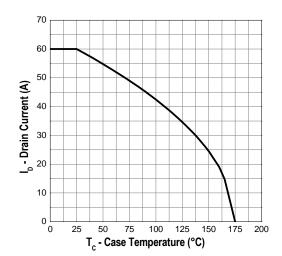
Capacitance



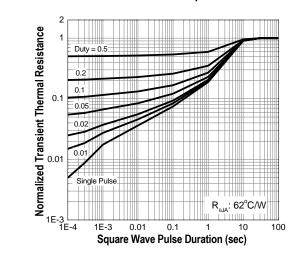


SG30N09Q

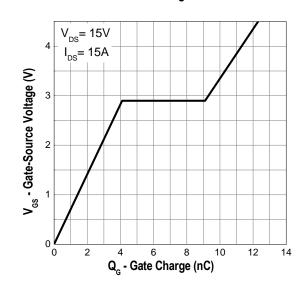
30V N-Channel Power MOSFET



Transient Thermal Impedance



Gate Charge



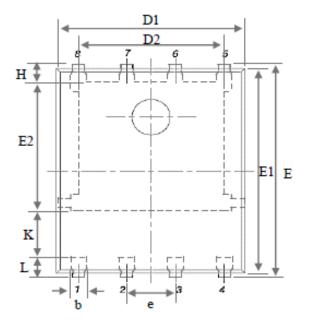


Marking Information

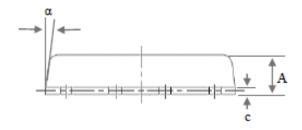
PDFN 5x6-8L (Q)	Marking Rule
Laser Marking	Line 1 : Device
	SG30N09Q
SG30N09Q YYMMXXX	Line 2 : Date Code YYMMXXX YY : Year Code MM : Month Code XXX : Serial Number



Package of Dimension



Symbol	Min	Nor	Max	
Α	0.90	1.04	1.17	
b	0.33	0.42	0.51	
С	0.06	0.20	0.35	
D1	4.80	5.10	5.40	
D2	3.61	3.96	4.31	
E	5.90	6.03	6.15	
E1	5.65	5.75	5.85	
E2	3.30	3.54	3.78	
е	1.27 BSC			
Η	0.38	0.50	0.61	
L	0.38	0.55	0.71	
L1	0.05	0.15	0.25	



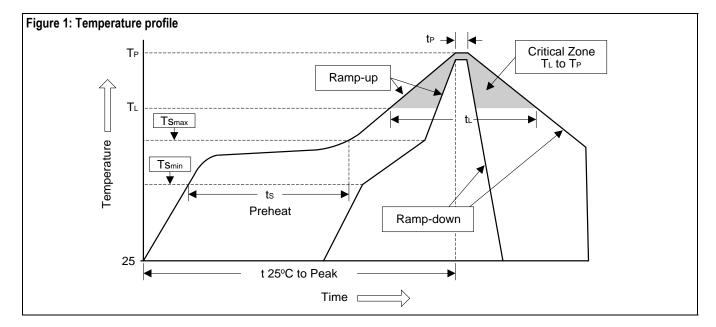
1. All dimension are in millimeters.

2. Dimension does not include burrs and mold flash/protrusions.



Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate $(T_L \text{ to } T_P)$	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t _L)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t _P)	10 10 00 300	2010 40 300
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



Important Notice

© Silicongear Corporation

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Silicongear cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in an Silicongear product. No circuit patent licenses, copyrights, mask work rights, or other intellectual property rights are implied.

Silicongear Corporation, its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Silicongear"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Silicongear makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Silicongear disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Silicongear's knowledge of typical requirements that are often placed on Silicongear products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Silicongear's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Silicongear products are not designed for use in medical, life-saving, or lifesustaining applications or for any other application in which the failure of the Silicongear product could result in personal injury or death. Customers using or selling Silicongear products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Silicongear and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Silicongear or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Silicongear personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Silicongear. Product names and markings noted herein may be trademarks of their respective owners.

Silicongear and the Silicongear logo are trademarks of Silicongear Corporation. All other brand and product names appearing in this document are registered trademarks or trademarks of their respective holders.